

TANCERAM® chip capacitors can replace tantalum capacitors in many applications and offer several key advantages over traditional tantalums. Because TANCERAM® capacitors exhibit extremely low ESR, equivalent circuit performance can often be achieved using considerably lower capacitance values. Low DC leakage reduces current drain, extending the battery life of portable products. TANCERAM® high DC breakdown voltage ratings offer improved reliability and eliminate large voltage de-rating common when designing with tantalums.

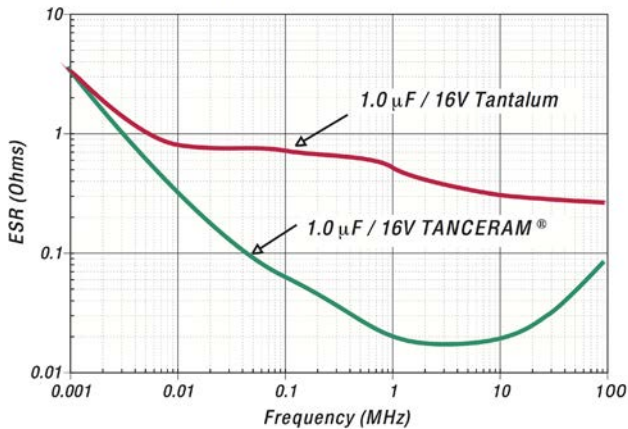
## ADVANTAGES

- Low ESR
- Higher Surge Voltage
- Reduced CHIP Size
- Higher Insulation Resistance
- Low DC Leakage
- Non-polarized Devices
- Improved Reliability
- Higher Ripple Current

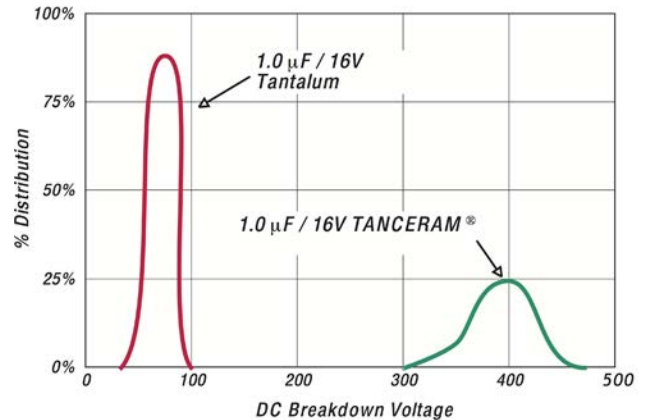
## APPLICATIONS

- Switching Power Supply Smoothing (Input/Output)
- DC/DC Converter Smoothing (Input/Output)
- Backlighting Inverters
- General Digital Circuits

Typical ESR Comparison



Typical Breakdown Voltage Comparison

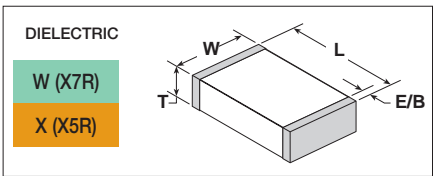


## HOW TO ORDER TANCERAM®

Part number written: 100R15X106MV4E

100	R15	X	106	M	V	4	E
<b>VOLTAGE</b>	<b>SIZE</b>	<b>DIELECTRIC</b>	<b>CAPACITANCE</b>	<b>TOLERANCE</b>	<b>TERMINATION</b>	<b>MARKING</b>	<b>PACKING</b>
6R3 = 6.3 V 100 = 10 V 160 = 16 V 250 = 25 V 500 = 50 V 101 = 100 V	See Chart	W = X7R X = X5R	1st two digits are significant; third digit denotes number of zeros. 105 = 1.00 µF 476 = 47.0 µF 107 = 100 µF	K = ±10% M = ±20%	V = Nickel Barrier with 100% Tin Plating (Matte)  T = SnPb* (*available on select parts)	4 = Unmarked	Code Type Reel E Plastic 7" T Paper 7" Tape specifications conform to EIA RS481

## CAPACITANCE SELECTION



EIA / JDI	INCHES	(mm)	VDC	1.0 µF	1.5 µF	2.2 µF	3.3 µF	4.7 µF	10 µF	22 µF	47 µF	100 µF	220 µF	
				W	X	W	X	W	X	W	X	W	X	
0201 R05 -	L W T EB	.024 ±.001 .011 ±.001 .013 Max. .004 Min.	(0.60 ±.03) (0.28 ±.03) (0.33 Max.) (0.10 Min.)	Dielectric										
				10										
				6.3										
				4										
				35										
0402 R07 -	L W T EB	.039 ±.002 .020 ±.002 .022 Max. .002 Min.	(0.99 ±.05) (0.51 ±.05) (0.55 Max.) (0.05 Min.)	35										
				25										
				16										
				10										
				6.3										
0603 R14 -	L W T EB	.063 ±.004 .031 ±.004 .037 Max. .006 Min.	(1.60 ±.10) (0.79 ±.10) (0.93 Max.) (0.15 Min.)	50										
				35										
				25										
				16										
				10										
0805 R15 -	L W T EB	.079 ±.012 .049 ±.008 .057 Max. .008 Min.	(2.01 ±.30) (1.24 ±.20) (1.44 Max.) (0.20 Min.)	50										
				35										
				25										
				16										
				10										
1206 R18 -	L W T EB	.126 ±.012 .063 ±.008 .071 Max. .010 Min.	(3.20 ±.30) (1.60 ±.20) (1.80 Min.) (0.25 Min.)	50										
				35										
				25										
				16										
				10										
1210 S41 -	L W T EB	.126 ±.012 .098 ±.012 .106 Max. .012 Min.	(3.20 ±.30) (2.49 ±.30) (2.69 Max.) (0.30 Min.)	50										
				35										
				25										
				16										
				10										
1812 S43 -	L W T EB	.177 ±.016 .126 ±.012 .118 Max. .012 Min.	(4.50 ±.41) (3.20 ±.30) (2.99 Max.) (0.30 Min.)	50										
				25										
2220 S47 -	L W T EB	.220 ±.016 .197 ±.016 .118 Max. .012 Min.	(5.59 ±.41) (3.20 ±.30) (2.99 Max.) (0.30 Min.)	50										
				25										

"K" OR "M" TOLERANCE, 0201 ONLY AVAILIABLE IN M ONLY "M" TOLERANCE

### ELECTRICAL CHARACTERISTICS

DIELECTRIC:	X7R	X5R
TEMPERATURE COEFFICIENT:	±15% (-55 to +125°C)	±15% (-55 to +85°C)
DISSIPATION FACTOR:	For ≥ 50 VDC: 5% max. For ≤ 35 VDC: 10% max.	For ≥ 50 VDC: 5% max. For ≤ 35 VDC: 10% max.
INSULATION RESISTANCE (MIN. @ 25°C, WVDC)	100 ΩF or 10 GΩ, whichever is less	
DIELECTRIC STRENGTH:	2.5 X WVDC, 25°C, 50mA max.	
TEST CONDITIONS:	Capacitance values ≤ 10 µF: 1.0kHz±50Hz @ 1.0±0.2 Vrms Capacitance values > 10 µF: 120Hz±10Hz @ 0.5V±0.1 Vrms	
OTHER:	See page 81 for additional dielectric specifications.	

